



N-Channel Silicon MOSFET

# CPH3439 — General-Purpose Switching Device Applications

## Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

## Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		4.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	18	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	1.0	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2.5A	4.2	7		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =2.5A, V <sub>GS</sub> =4.5V		32	45	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =2.5A, V <sub>GS</sub> =4V		33	46	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		44	61	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, f=1MHz		748		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V, f=1MHz		95		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =10V, f=1MHz		82		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		15		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		52		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		90		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		65		ns

Marking : ZS

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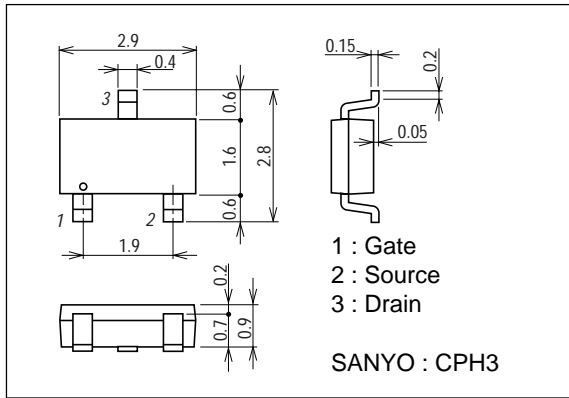
# CPH3439

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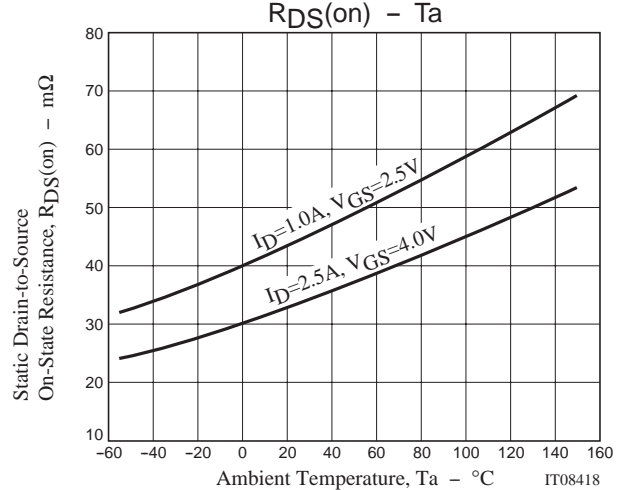
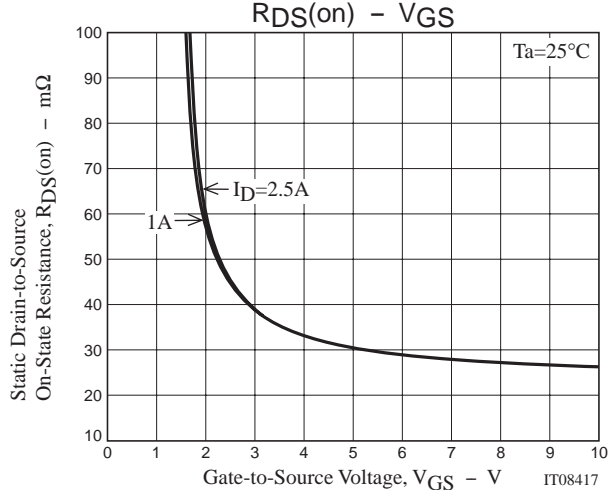
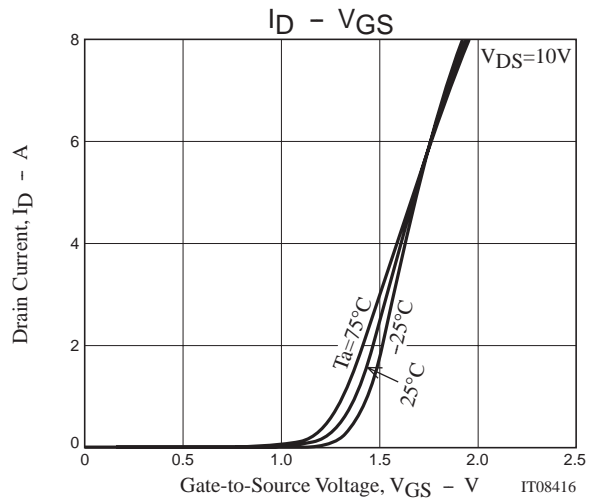
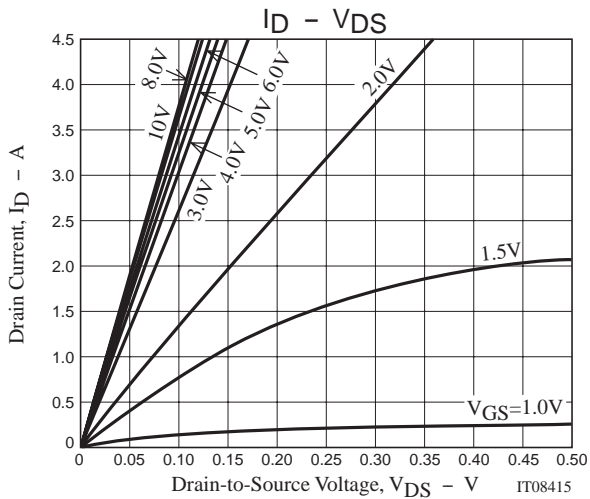
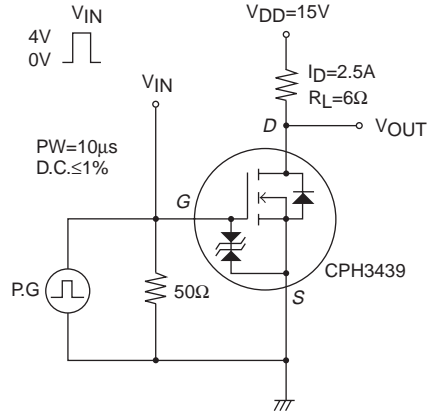
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4.5A		8.6		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4.5A		1.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4.5A		2.4		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =4.5A, V <sub>GS</sub> =0		0.85	1.2	V

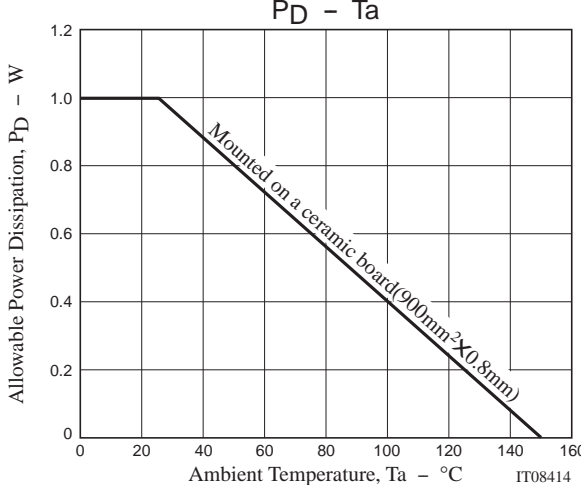
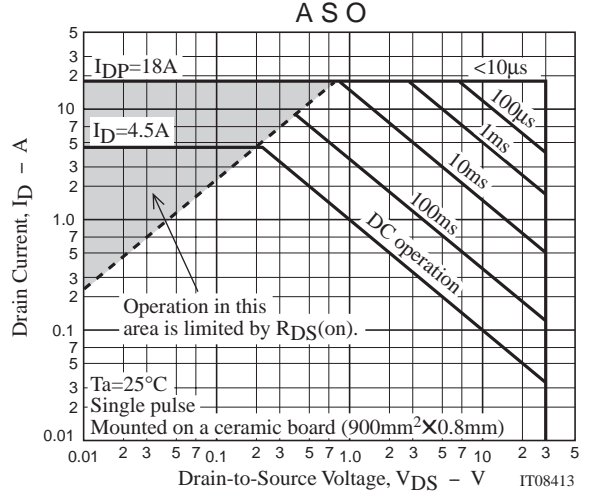
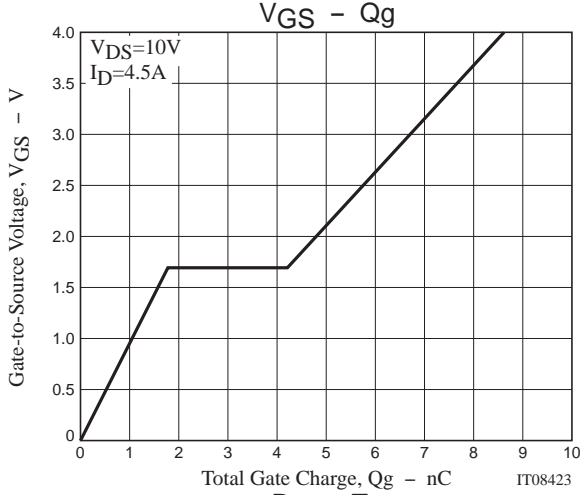
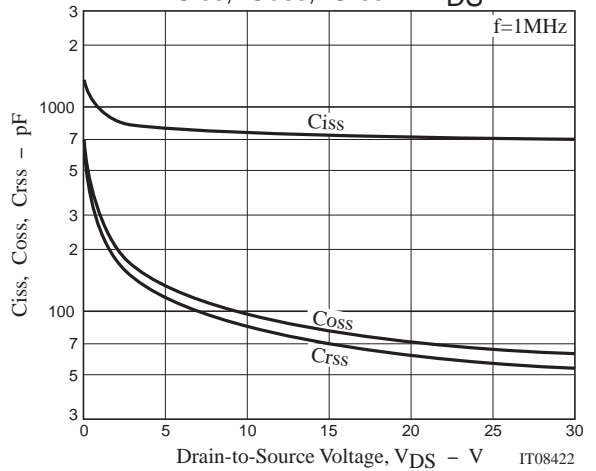
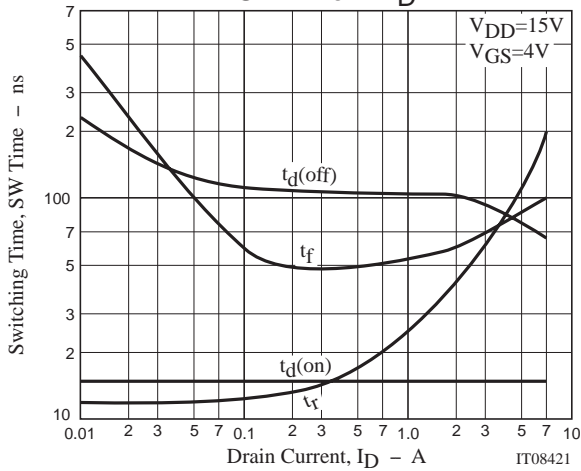
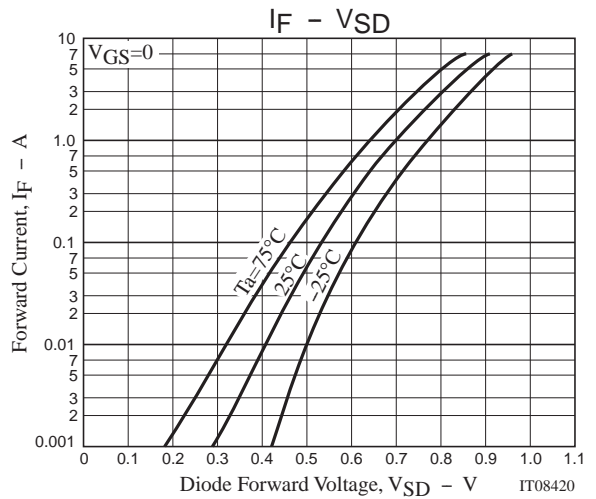
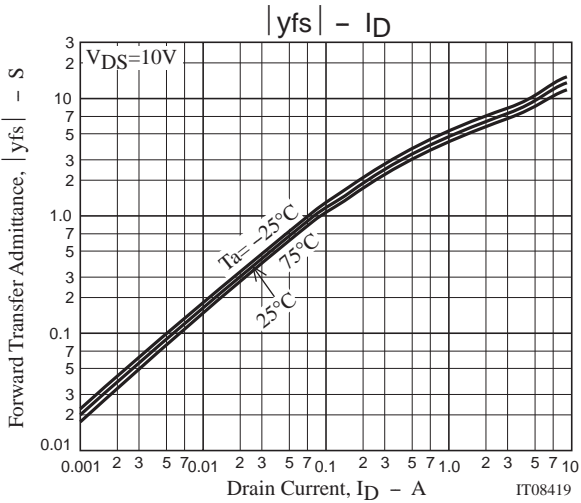
## Package Dimensions

unit : mm  
2152A



## Switching Time Test Circuit





Note on usage : Since the CPH3439 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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